

20V N-Channel Enhancement Mode MOSFET

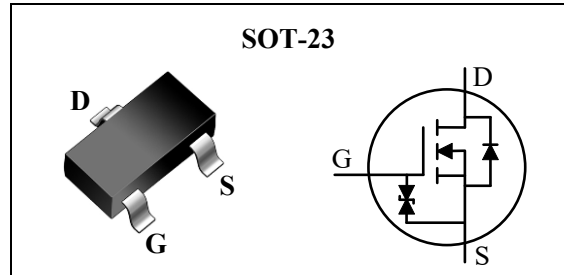
General Features

- $V_{DS} = 20V, I_D = 0.75A$
- $R_{DS(on)(Typ.)}: 182m\Omega @ V_{GS} = 4.5V$
- Advanced Trench Technology
- Excellent $R_{DS(on)}$ And Low Gate Charge
- Low Threshold Voltage
- ESD Rating: HBM 2.0KV
- RoHS Compliant
- Halogen-free Available

BV_{DSS}	$R_{DS(on)(Typ.)}$	I_D
20V	182m Ω	0.75A

Applications

- Load Switch
- PWM Application
- Notebook
- Battery Protection
- Hand-held Instruments
- Power Management
- DC/DC Conversion



Ordering Information

Part Number	Package	Marking	Remark
FTZ0P2N02G	SOT-23	0P2N02	Halogen Free

Absolute Maximum Ratings

$T_A = 25^\circ C$ unless otherwise specified

Symbol	Parameter	FTZ0P2N02G	Unit
V_{DSS}	Drain-to-Source Voltage ^[1]	20	V
V_{DGS}	Drain-to-Gate Voltage ^[1]	20	V
V_{GS}	Gate-to-Source Voltage	± 10	V
I_D	Continuous Drain Current ^[2]	0.75	A
I_{DM}	Pulsed Drain Current ^[3]	3	A
P_D	Power Dissipation ^[4]	0.5	W
E_{AS}	Avalanche Energy, Single Pulse ^[5]	0.36	mJ
T_L	Soldering Temperature Distance of 1.6mm from case for 10 seconds	300	$^\circ C$
T_J & T_{STG}	Operating and Storage Temperature Range	-55 to 150	$^\circ C$

Caution: Stresses beyond those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Thermal Characteristics

Symbol	Parameter	FTZ0P2N02G	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	250	$^\circ C/W$

Electrical Characteristics

OFF Characteristics

 $T_A = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	20	--	--	V	$V_{GS} = 0V, I_D = 250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	--	--	1	μA	$V_{DS} = 20V, V_{GS} = 0V$
I_{GSS}	Gate-to-Source Leakage Current	--	--	10	μA	$V_{GS} = 10V, V_{DS} = 0V$
		--	--	-10		$V_{GS} = -10V, V_{DS} = 0V$

ON Characteristics

 $T_A = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	--	182	228	$m\Omega$	$V_{GS} = 4.5V, I_D = 0.5A$ [6]
		--	222	278		$V_{GS} = 2.5V, I_D = 0.4A$ [6]
$V_{GS(th)}$	Gate Threshold Voltage	0.3	0.7	1.5	V	$V_{GD} = 0V, I_D = 250\mu A$

Dynamic Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
C_{iss}	Input Capacitance	--	47	--	pF	$V_{GS} = 0V,$ $V_{DS} = 10V,$ $f = 1.0MHz$
C_{oss}	Output Capacitance	--	18	--		
C_{rss}	Reverse Transfer Capacitance	--	11	--		
R_G	Gate Resistance	--	18	--	Ω	$V_{GS} = 0V, V_{DS} = 0V,$ $f = 1.0MHz$
Q_g	Total Gate Charge	--	1.67	--	nC	$V_{GS} = 0 \text{ to } 10V,$ $V_{DD} = 10V,$ $I_D = 0.1A$
Q_{gs}	Gate-to-Source Charge	--	0.18	--		
Q_{gd}	Gate-to-Drain (Miller) Charge	--	0.22	--		

Resistive Switching Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$t_{d(on)}$	Turn-on Delay Time	--	2.24	--	ns	$V_{GS} = 10V,$ $V_{DD} = 10V,$ $I_D = 0.1A,$ $R_G = 6\Omega$
t_r	Rise Time	--	2.16	--		
$t_{d(off)}$	Turn-off Delay Time	--	9.6	--		
t_f	Fall Time	--	10.4	--		



FTZ0P2N02G

Provisional Datasheet

Source-Drain Diode Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min	Typ.	Max.	Unit	Test Conditions
V_{SD}	Diode Forward Voltage	--	--	1.2	V	$I_{SD} = 0.5\text{A}$, $V_{GS} = 0\text{V}$

NOTE:

[1] $T_J = +25^\circ\text{C}$ to $+150^\circ\text{C}$.

[2] $T_C = +25^\circ\text{C}$.

[3] Repetitive rating, pulse width limited by maximum junction temperature.

[4] $T_C = +25^\circ\text{C}$.

[5] E_{AS} condition: Starting $T_J = 25^\circ\text{C}$, $V_{DD} = 10\text{V}$, $V_{GS} = 10\text{V}$, $R_G = 25\Omega$, $L = 0.5\text{mH}$, $I_{AS} = 1.2\text{A}$.

[6] Pulse width $\leq 380\mu\text{s}$, duty cycle $\leq 2\%$.

Typical Characteristics

Figure 1. Maximum Power Dissipation vs. Case Temperature

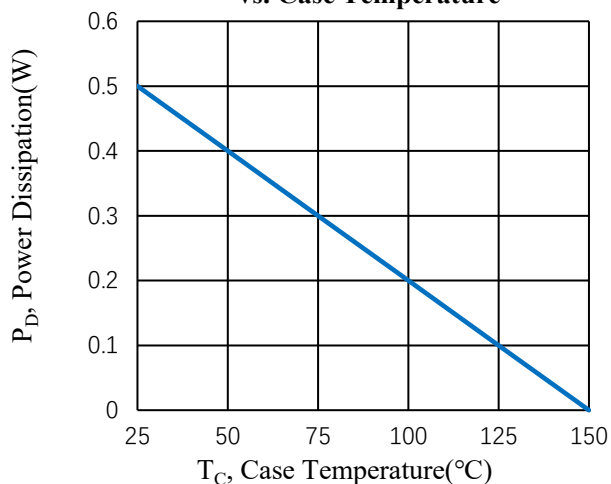


Figure 2. Maximum Continuous Drain Current vs. Case Temperature

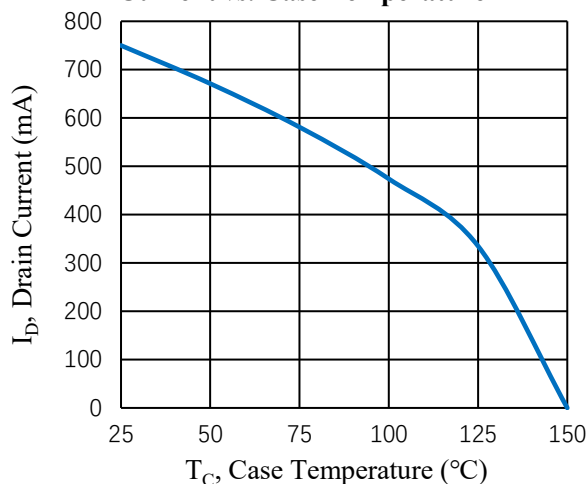


Figure 3. Typical Output Characteristics

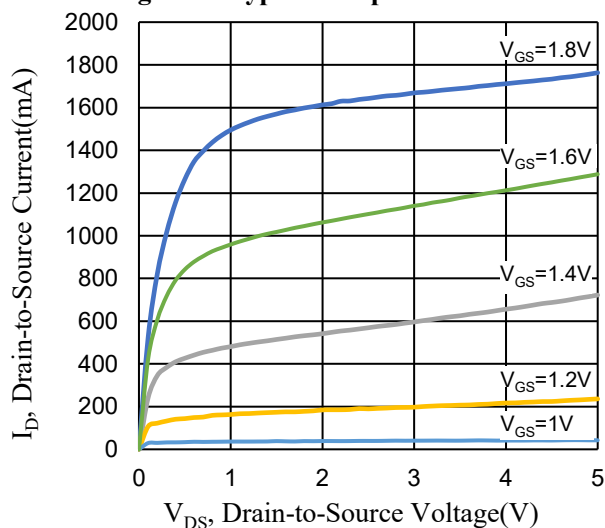


Figure 4. Typical Transfer Characteristics

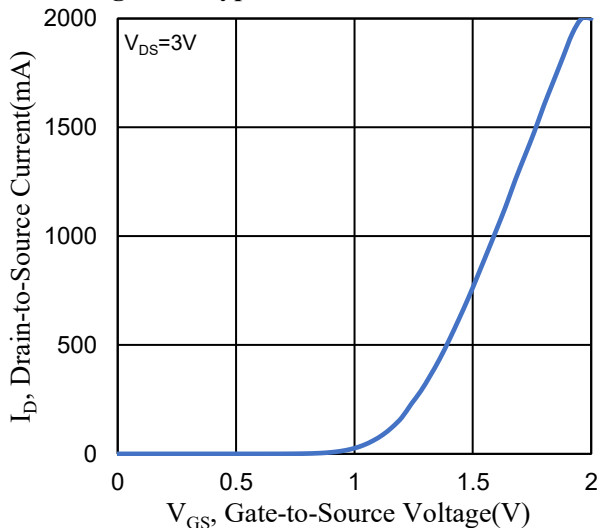


Figure 5. Typical Capacitance vs. Drain-to-Source Voltage

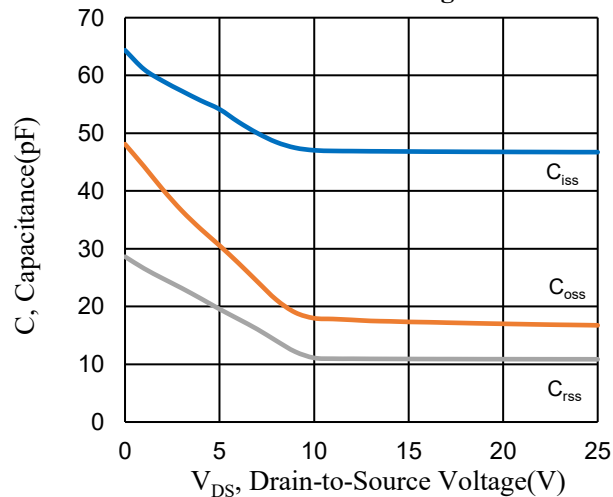
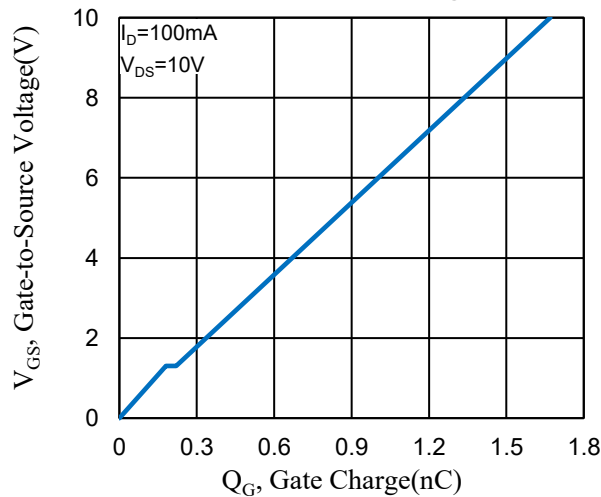
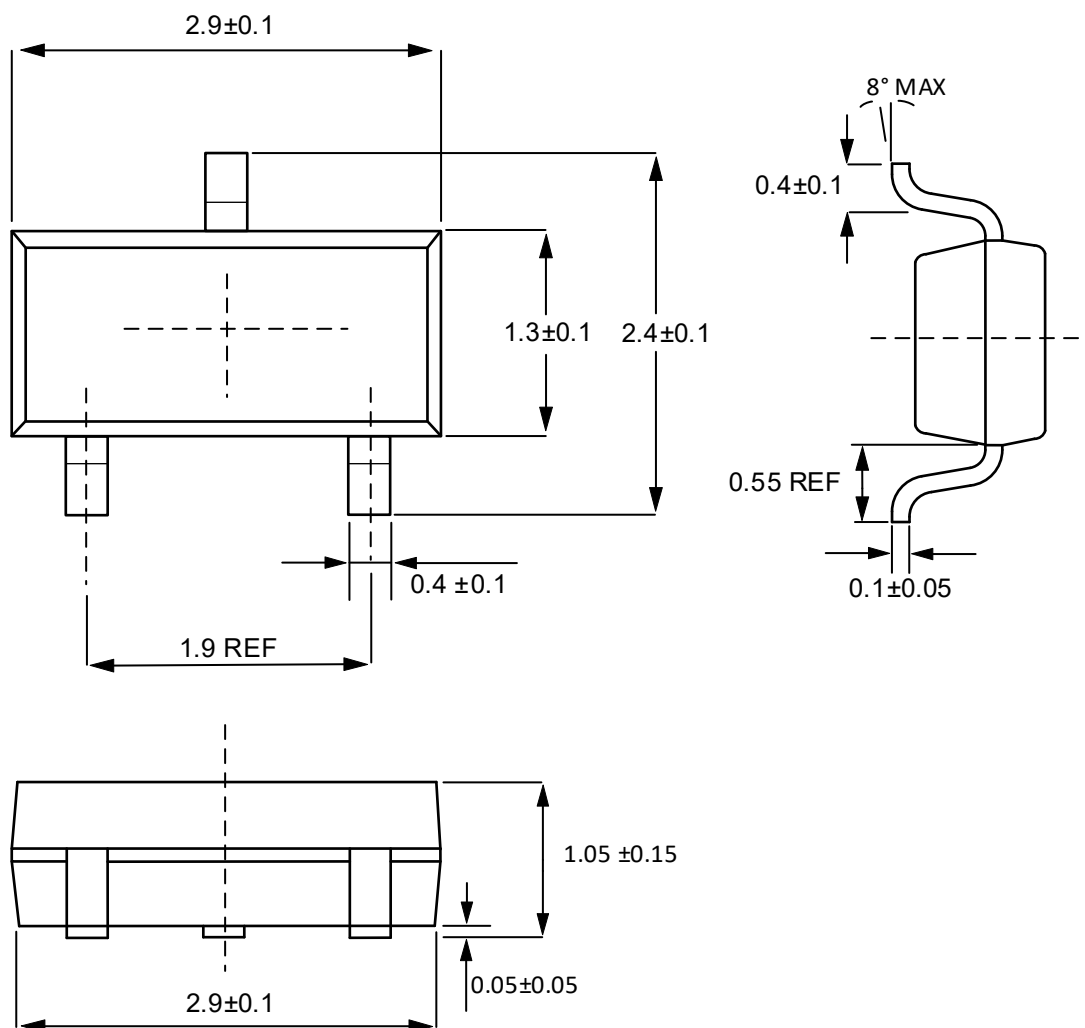


Figure 6. Typical Gate Charge vs. Gate-to-Source Voltage



Package Dimensions

SOT-23





Published by
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